

a means for transporting said substrate among said first, second, third and fourth chambers,

wherein said multi-chamber system is capable of depositing said gate insulating film on said semiconductor film irradiated with said laser light.

102. A multi-chamber system according to claim 101 wherein said third chamber is selected from apparatuses consisting of a plasma CVD apparatus, a low pressure CVD apparatus, an atmospheric pressure CVD apparatus and a sputtering film formation apparatus.

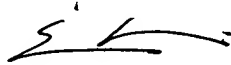
103. A multi-chamber system according to claim 102 wherein said ~~apparatuses are capable of forming a silicon oxide film.~~

REMARKS

Claims 8, 9, 12, 13, 21, 23, and 47-79 have been canceled and new claims 80-103 have been added in this Continued Prosecution Application.

Examination on the merits is requested.

Respectfully submitted,



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